

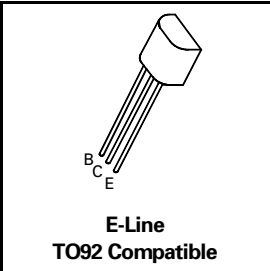
# PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

**FXT550**

ISSUE 1 – SEPT 93

**FEATURES**

- \* 45 Volt  $V_{CEO}$
- \* 1 Amp continuous current
- \*  $P_{tot} = 1$  Watt



REFER TO ZTX550 FOR GRAPHS

**ABSOLUTE MAXIMUM RATINGS.**

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-60	V
Collector-Emitter Voltage	$V_{CEO}$	-45	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-2	A
Continuous Collector Current	$I_C$	-1	A
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}C$

**ELECTRICAL CHARACTERISTICS (at  $T_{amb} = 25^{\circ}C$ ).**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60			V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	-45			V	$I_C = -10mA, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu A, I_C = 0$
Collector Cut-Off Current	$I_{CBO}$			-0.1	$\mu A$	$V_{CB} = -45V, I_E = 0$
Emitter Cut-Off Current	$I_{EBO}$			-0.1	$\mu A$	$V_{EB} = -4V, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.25	V	$I_C = -150mA, I_B = -15mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.1	V	$I_C = -150mA, I_B = -15mA^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100 15		300		$I_C = -150mA, V_{CE} = -10V^*$ $I_C = -1A, V_{CE} = -10V^*$
Transition Frequency	$f_T$	150			MHz	$I_C = 50mA, V_{CE} = -10V$ $f = 100MHz$
Output Capacitance	$C_{obo}$			25	pF	$V_{CB} = -10V, f = 1MHz$

\*Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$